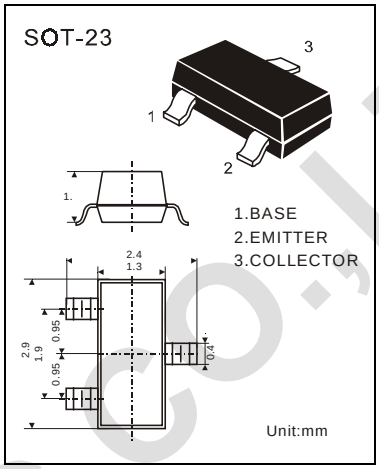
WEJ®

RoHS

2SC945LT1

NPN EPITAXIAL SILICON TRANSISTOR

* Collector Current: Ic= 150mA
* Collector-Emitter Voltage:Vce= 50V
* High Total Power Dissipation:Pc=225mW
* High Hfe And Good Linearity



ABSOLUTE MAXIMUM RATINGS at Ta=25℃

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	60	V
Collector-Emitter Voltage	Vceo	50	V
Collector Current	Ic	150	mA
Collector Dissipation Ta=25℃*	P_D	225	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55-150	℃

ELECTRICAL CHARACTERISTICS at Ta=25℃

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	60			V	Ic=100uA Ie=0
Collector-Emitter Breakdown Voltage#	BVceo	50			V	Ic= 1mA Ib=0
Collector-Base Cutoff Current	Icbo			100	nA	Vcb= 60V Ie=0
DC Current Gain	Hfe	70		700		Vce= 6V Ic= 1mA
Collector-Emitter Saturation Voltage	Vce(sat)			0.3	V	Ic= 100mA Ib= 10mA
Output Capacitance	Cob		2.2	3.5	PF	Vcb= 10V Ie=0 f=1MHz
Current Gain-Bandwidth Product	f_T		150		MHz	Vce= 5V Ic= 10mA

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25℃.

\# Pulse Test : Pulse Width ≤300uS,Duty cycle ≤2%

DEVICE MARKING:

2SC945LT1=HF